

OKI semiconductor

MSM28F101

1 M BIT (128K x 8) CMOS FLASH MEMORY

GENERAL DESCRIPTION

The MSM28F101 is a high speed 128K x 8-bit Flash erasable and electrically reprogrammable memory, ideally suited for systems requiring on-board code updates. Flash erasable means an electrical erase of the full memory contents, typically within 1 second.

The MSM28F101 features "Speed Programming" capability, by which four bytes of the same data can be programmed simultaneously. By using this mode, the total erase time is reduced.

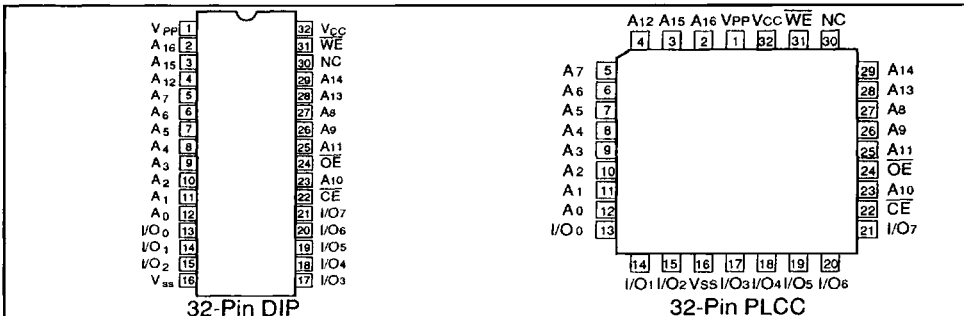
It is pin compatible with EPROM devices and Read timings are fully compatible with EPROM operation. Programming and Erase are performed through an operation and verify algorithm. The instructions are input via the I/O bus, using a two write cycle scheme. Address and Data are latched to free the I/O bus and address bus during write operation.

The MSM28F101 is packaged in a 32-pin plastic DIP, or in a 32-pin PLCC package.

FEATURES

- Fast access time: 120/150/200ns
- Low current requirements:
Active: 30mA max (CMOS level)
Standby: 100µA max (CMOS level)
Standby: 1mA max (TTL level)
- High speed programming
10µs/byte typical
- 131,072 X 8-bit configuration
- TTL compatible Input/Output
- 12.0V programming
- JEDEC approved 32-pin DIP or 32-pin PLCC
- 1,000 cycle endurance;
optional 10,000 cycle endurance
- 10 year data retention
- Electronic signature

PIN CONFIGURATION (TOP VIEW)



Pin Names	Function
A ₀ - A ₁₆	Address Input
CE	Chip Enable
OE	Output Enable
WE	Write Enable
I/O ₀ - I/O ₇	Data Byte/Instruction Register
V _{CC}	Read Voltage Supply
V _{SS}	Ground
V _{PP}	Program Voltage Supply

These specifications may be changed without notification.

